MSKSEMI 美森科







T\/C



TSS



MOV



GDT



PIFF

MMBT2907AM3T5G-MS

Product specification





General Features

Epitaxial planar die construction
Complementary PNP Type available(MMBT2222AM)

Reference News

PACKAGE OUTLINE	Foot position analysis	Marking
W.F.E.F.M.	1. BASE 2.EMITTER 3.COLLECTOR	AC
SOT-723		



MAXIMUM RATINGS(Ta = 25°C)

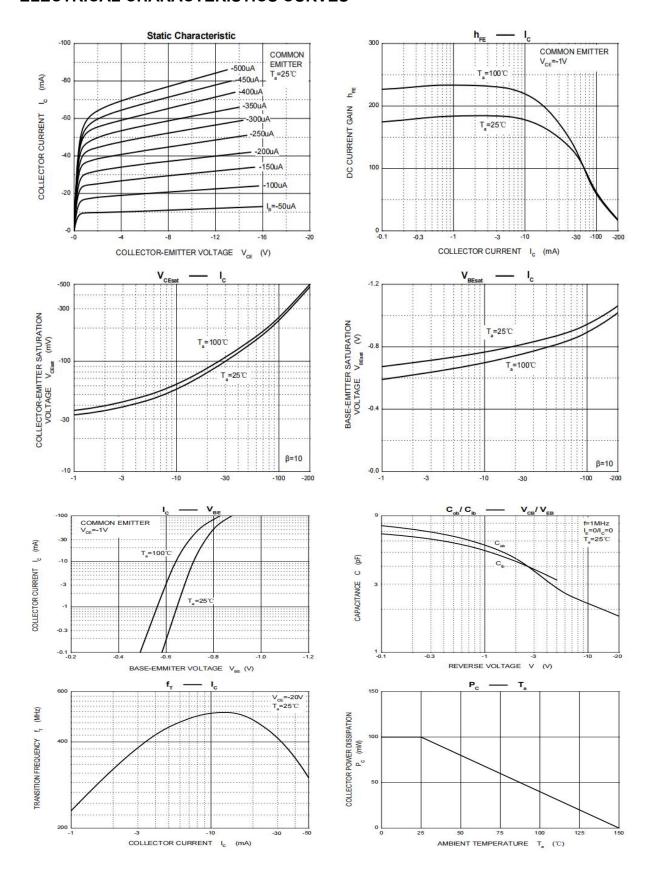
Symbol	Parameter	Value	Unit
V сво	Collector-Base Voltage	-60	V
VCEO	Collector-Emitter Voltage	-60	V
V EBO	Emitter-Base Voltage	-5	V
lc	Collector Current -Continuous	-0.5	А
Pc	Power Dissipation	100	mW
$R_{_{\Theta JA}}$	Thermal Resistance from Junction to Ambient	1250	°C/W
Tu	Junction Temperature	150	°C
Tstg	storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25 ℃ unless otherwise

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	Ic=-10μA,I∈=0	-60			V
Collector-emitter breakdown voltage	V(BR)CEO	Ic=-1mA,I _B =0	-60			V
Emitter-base breakdown voltage	V(BR)EBO	Iε=-10μΑ,Ic=0	-5			V
Collector cut-off current	Ісво	V _{CB} =-40V,I _E =0			-100	nA
Collector cut-off current	ICEX	VCE=-30V,VEB(off)=-3V			-50	Α
Emitter cut-off current	ІЕВО	V _{EB} =-5V,I _C =0			-100	nA
DC current gain	hFE(1)	VcE=-1V,Ic=-10mA	100		300	
	hFE(2)	VcE=-1V,Ic=-50mA	60			
	hFE(3)	VcE=-2V,I c=-100mA	30			
Collector-emitter saturation voltage	VCE(sat)	Ic=-50mA,Iв=-5mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	Ic=-50mA,Iв=-5mA			-0.95	V
Transition frequency	т	Vc=-20V,lc=-10mA,f=100MHz	300			MHz
Delay time	t d	Vcc=-3V,VBE(off)=-0.5V,			35	ns
Rise time	tr	Ic=-10mA, I _{B1} =I _{B2} =-1mA			35	ns
Storage time	ts	Vcc=-3V,Ic=-10mA			225	ns
Fall time	tf	I _{B1} =I _{B2} =-1mA			75	ns

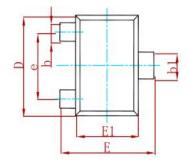


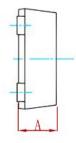
ELECTRICAL CHARACTERISTICS CURVES

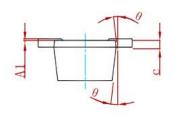




PACKAGE MECHANICAL DATA

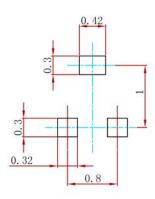






Symbol	Dimensions	In Millimeters	Dimensions	In Inches
Symbol	Min.	Max.	Min.	Max.
Α	0.430	0.500	0.017	0.020
A1	0.000	0.050	0.000	0.002
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
С	0.080	0.150	0.003	0.006
D	1.150	1.250	0.045	0.049
Е	1.150	1.250	0.045	0.049
E1	0.750	0.850	0.030	0.033
е	0 800	TYP	0 031	TYP
θ	7° F	REF.	7° R	EF.

Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMBT2907AM3T5G-MS	SOT-723	8000



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